

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	12	V
Gate-Source Voltage			V _{GSS}	±6	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	2.0	A
		T _A = +70°C		1.6	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.39	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	320	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	141	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	49	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	12	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±6V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.35	0.42	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	119	150	mΩ	V _{GS} = 4.5V, I _D = 1A
			141	185		V _{GS} = 2.5V, I _D = 1A
			175	210		V _{GS} = 1.8V, I _D = 1A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	115	—	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	25	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	23	—	pF	
Gate Resistance	R _G	—	90	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	1.4	—	nC	V _{DS} = 4V, V _{GS} = 4.5V, I _D = 1A
Gate-Source Charge	Q _{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q _{GD}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.0	—	ns	V _{GS} = 6V, V _{DS} = 4V, R _G = 1Ω, I _D = 1A
Turn-On Rise Time	t _R	—	7.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	44	—	ns	
Turn-Off Fall Time	t _F	—	19	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

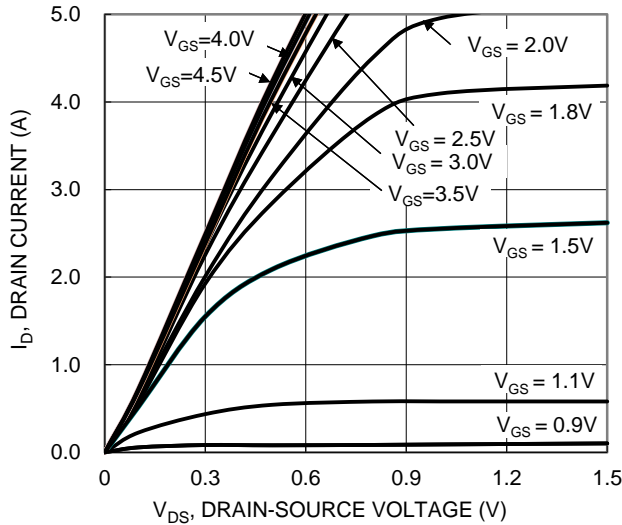


Figure 1. Typical Output Characteristic

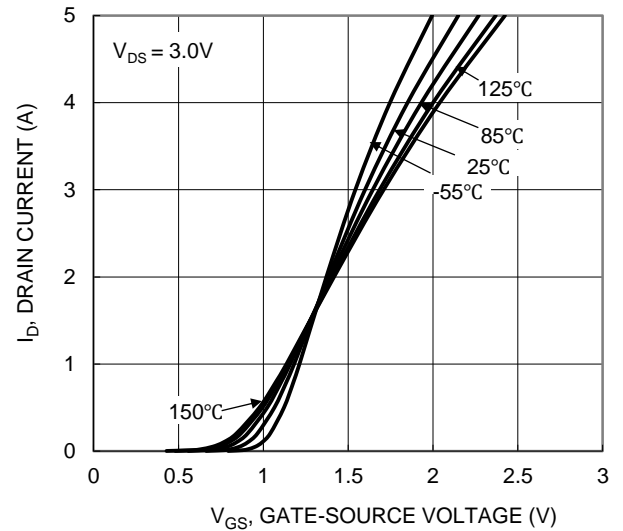


Figure 2. Typical Transfer Characteristic

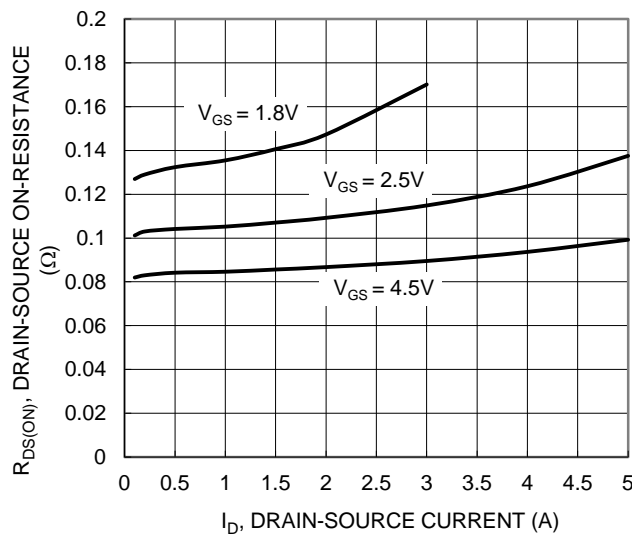


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

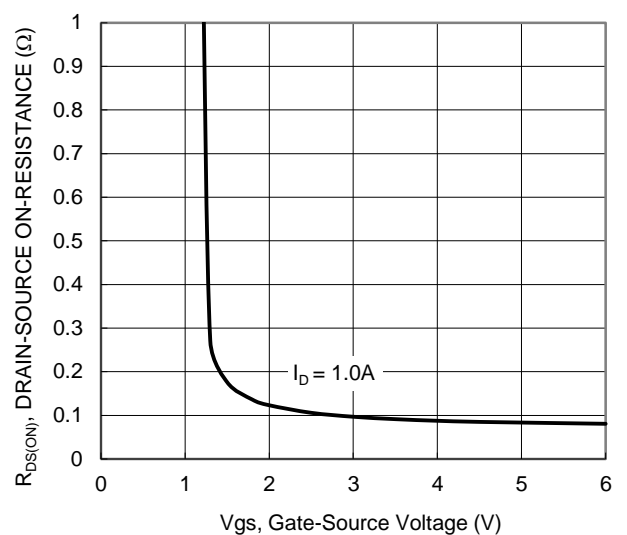


Figure 4. Typical Transfer Characteristic

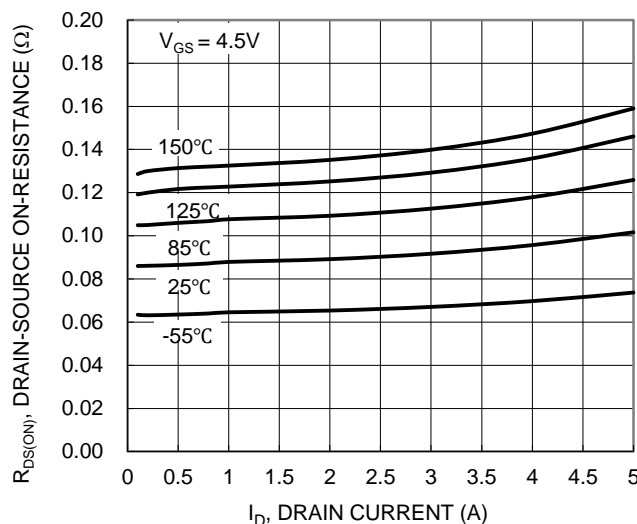


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

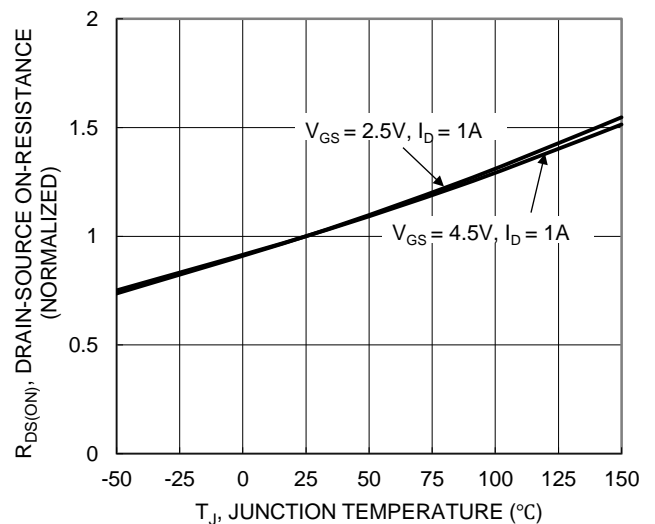


Figure 6. On-Resistance Variation with Temperature

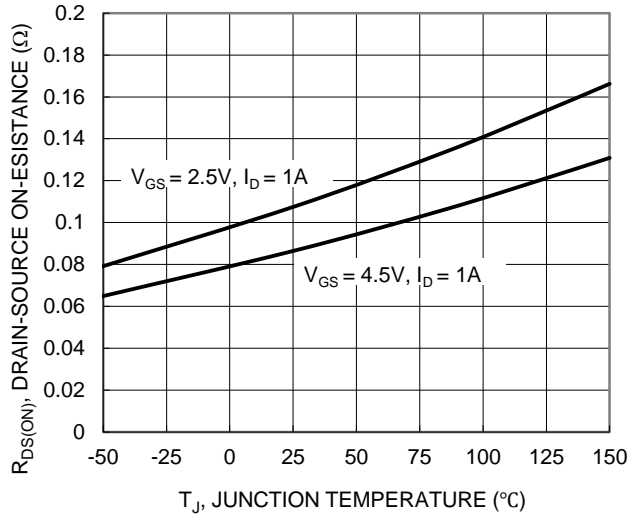


Figure 7. On-Resistance Variation with Temperature

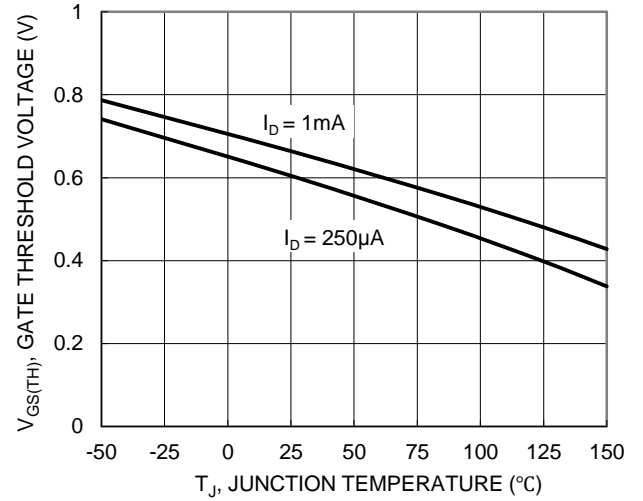


Figure 8. Gate Threshold Variation vs. junction Temperature

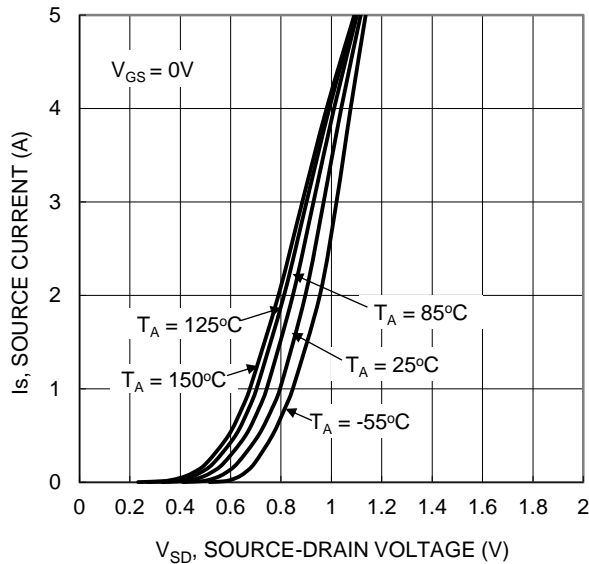


Figure 9. Diode Forward Voltage vs. Current

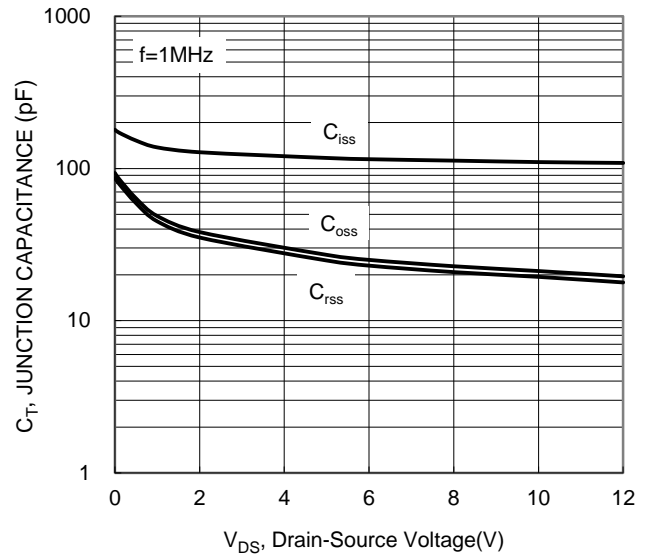


Figure 10. Typical Junction Capacitance

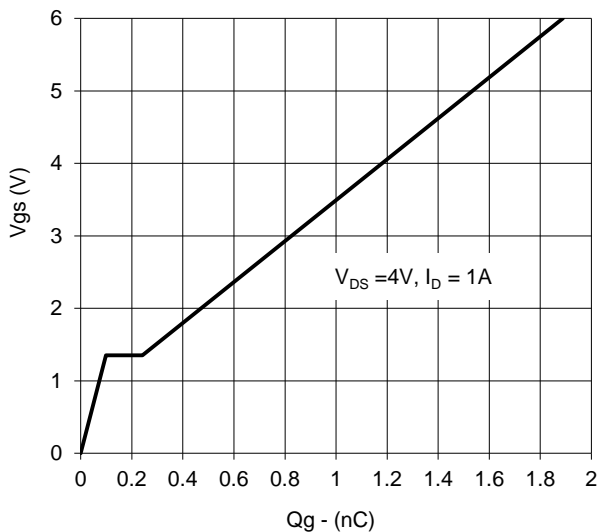


Figure 11. Gate Charge

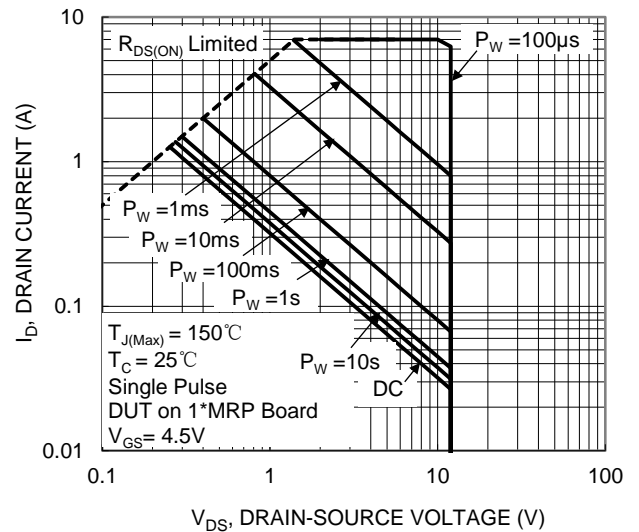


Figure 12. SOA, Safe Operation Area

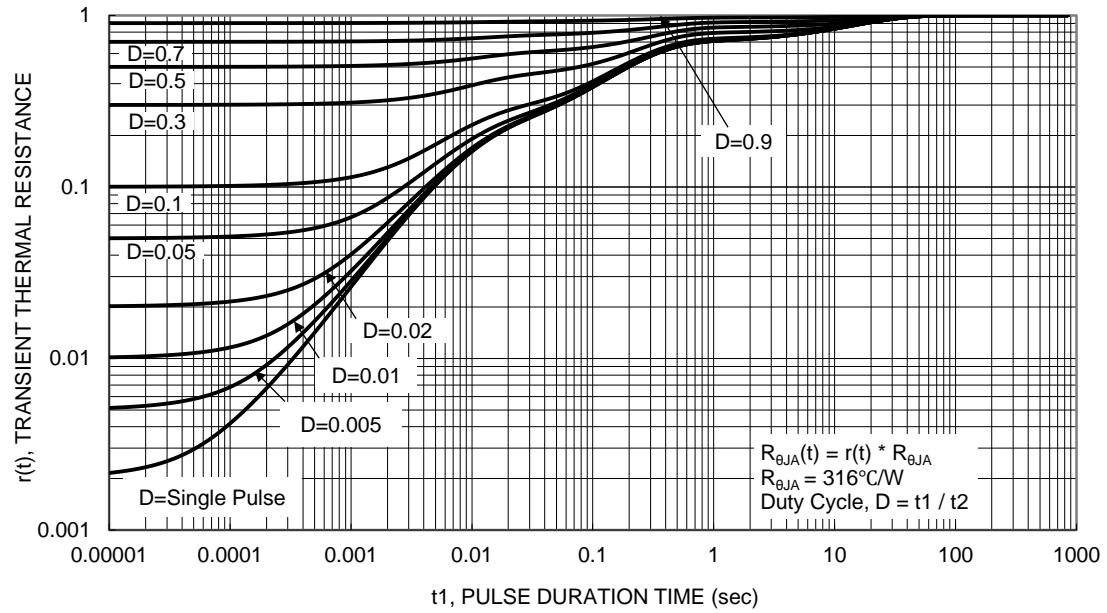
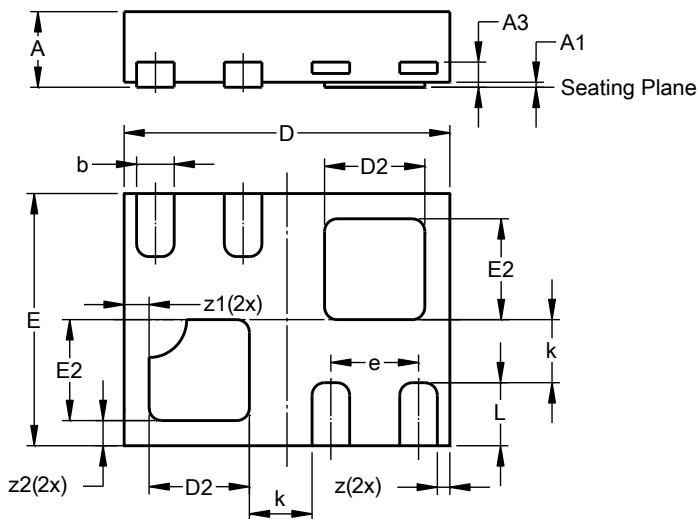


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1310-6 (Type B)

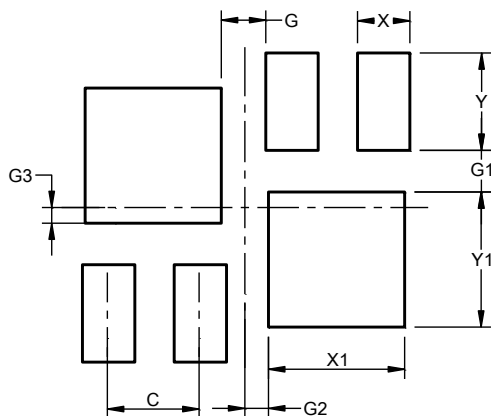


X2-DFN1310-6 (Type B)			
Dim	Min	Max	Typ
A	0.25	0.35	0.30
A1	0	0.05	0.02
A3	--	--	0.100
b	0.10	0.20	0.15
D	1.25	1.35	1.30
D2	0.30	0.50	0.40
E	0.95	1.05	1.00
E2	0.30	0.50	0.40
e	--	--	0.35
k	0.15	--	--
L	0.20	0.30	0.25
z	--	--	0.05
z1	--	--	0.10
z2	--	--	0.10
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1310-6 (Type B)



Dimensions	Value (in mm)
C	0.350
G	0.17
G1	0.16
G2	0.09
G3	0.06
X	0.20
X1	0.52
Y	0.375
Y1	0.52

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